

Wanjun Wang

List of Publications by Year in descending order

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43
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citing authors

#	ARTICLE	IF	CITATIONS
1	Low-threshold optically pumped lasing in highly strained germanium nanowires. Nature Communications, 2017, 8, 1845.	12.8	131
2	Wavelength-Flattened Directional Coupler Based Mid-Infrared Chemical Sensor Using Bragg Wavelength in Subwavelength Grating Structure. Nanomaterials, 2018, 8, 893.	4.1	42
3	Integrating GeSn photodiode on a 200 nm Ge-on-insulator photonics platform with Ge CMOS devices for advanced OEIC operating at 2 μ m band. Optics Express, 2019, 27, 26924.	3.4	28
4	Spiral Waveguides on Germanium-on-Silicon Nitride Platform for Mid-IR Sensing Applications. IEEE Photonics Journal, 2018, 10, 1-7.	2.0	23
5	Extracting more light for vertical emission: high power continuous wave operation of 1.3- μ m quantum-dot photonic-crystal surface-emitting laser based on a flat band. Light: Science and Applications, 2019, 8, 108.	16.6	22
6	Electromagnetically induced transparency-like effect in microring-Bragg gratings based coupling resonant system. Optics Express, 2016, 24, 25665.	3.4	20
7	Modal gain characteristics of a 2 μ m InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2017, 111, .	3.3	20
8	A 390 ps On-Wafer True-Time-Delay Line Developed by a Novel Micro-Coax Technology. IEEE Microwave and Wireless Components Letters, 2014, 24, 233-235.	3.2	18
9	Surface Plasmon Enhanced Nitrogen-Doped Graphene Quantum Dot Emission by Single Bismuth Telluride Nanoplates. Advanced Optical Materials, 2017, 5, 1700176.	7.3	18
10	Mid-Infrared, Ultra-Broadband, Low-Loss, Compact Arbitrary Power Splitter Based on Adiabatic Mode Evolution. IEEE Photonics Journal, 2019, 11, 1-11.	2.0	18
11	Compact silicon photonic hybrid ring external cavity (SHREC)/InGaSb-AlGaAsSb wavelength-tunable laser diode operating from 1881-1947 nm. Optics Express, 2020, 28, 5134.	3.4	17
12	A compact ultrabroadband polarization beam splitter utilizing a hybrid plasmonic Y-branch. IEEE Photonics Journal, 2016, , 1-1.	2.0	16
13	A Polarization Splitter and Rotator Based on a Partially Etched Grating-Assisted Coupler. IEEE Photonics Technology Letters, 2016, 28, 911-914.	2.5	15
14	Sub-kHz linewidth, hybrid III-V/silicon wavelength-tunable laser diode operating at the application-rich 1647-1690 nm. Optics Express, 2020, 28, 25215.	3.4	14
15	Investigation of regime switching from mode locking to Q-switching in a 2 μ m InGaSb/AlGaAsSb quantum well laser. Optics Express, 2018, 26, 8289.	3.4	13
16	Carrier selective solution processed molybdenum oxide silicon heterojunctions solar cells with over 12% efficiency. Semiconductor Science and Technology, 2020, 35, 075022.	2.0	13
17	1 μ m - N (N = 2, 8) Silicon Selector Switch for Prospective Technologies at the 2 μ m Waveband. IEEE Photonics Technology Letters, 2020, 32, 1127-1130.	2.5	12
18	Ligand size effects in two-dimensional hybrid copper halide perovskites crystals. Communications Materials, 2021, 2, .	6.9	12

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19	Hole selective WO _x and V ₂ O _x contacts using solution process for silicon solar cells application. Materials Chemistry and Physics, 2021, 273, 125101.	4.0	11
20	High-performance 1.06- μm InGaAs/GaAs double-quantum-well semiconductor lasers with asymmetric heterostructure layers. Semiconductor Science and Technology, 2019, 34, 055013.	2.0	9
21	High temperature characteristics of a 2 μm InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2019, 114, .	3.3	8
22	Wafer-Scale Demonstration of Low-Loss (\sim 40.43 dB/cm), High-Bandwidth ($>$ 38 GHz), Silicon Photonics Platform Operating at the C-Band. IEEE Photonics Journal, 2022, 14, 1-9.	2.0	8
23	Air-gapped microcoaxial transmission line for ultrawide band microwave and millimeter wave ICS. Microwave and Optical Technology Letters, 2014, 56, 1462-1465.	1.4	7
24	Low-Loss Microcoax-to-CPW Transition for Air-gapped Microcoaxial Passives. IEEE Microwave and Wireless Components Letters, 2015, 25, 585-587.	3.2	6
25	Experimental Demonstration of Thermally Tunable Fano and EIT Resonances in Coupled Resonant System on SOI Platform. IEEE Photonics Journal, 2018, 10, 1-8.	2.0	6
26	High-Photocurrent and Wide-Bandwidth UTC Photodiodes With Dipole-Doped Structure. IEEE Photonics Technology Letters, 2014, 26, 1952-1955.	2.5	5
27	Monolithic Fabrication of InGaAs/GaAs/AlGaAs Multiple Wavelength Quantum Well Laser Diodes via Impurity-Free Vacancy Disordering Quantum Well Intermixing. IEEE Journal of the Electron Devices Society, 2017, 5, 122-127.	2.1	5
28	Wafer-Level Characterization of Silicon Nitride CWDM (De)Multiplexers Using Bayesian Inference. IEEE Photonics Technology Letters, 2020, 32, 917-920.	2.5	5
29	On-Chip Air-Gapped Cavity Resonators and Filters for mm-Wave IC Applications. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2016, 6, 1549-1554.	2.5	4
30	Low-Loss Microcoaxial Rat-Race Hybrid for Si-Based Microwave Integrated Circuits. IEEE Microwave and Wireless Components Letters, 2016, 26, 162-164.	3.2	4
31	Temperature- and current-dependent spontaneous emission study on 2 μm InGaSb/AlGaAsSb quantum well lasers. Japanese Journal of Applied Physics, 2017, 56, 050310.	1.5	4
32	High-Speed and High-Responsivity InP-Based Uni-Traveling-Carrier Photodiodes. IEEE Journal of the Electron Devices Society, 2017, 5, 40-44.	2.1	4
33	Analysis of Compact Silicon Photonic Hybrid Ring External Cavity (SHREC) Wavelength-Tunable Laser Diodes Operating From 1881 \sim 1947 nm. IEEE Journal of Quantum Electronics, 2020, 56, 1-11.	1.9	4
34	SiN-SOI Multilayer Platform for Prospective Applications at 2 μm . IEEE Photonics Journal, 2019, 11, 1-9.	2.0	3
35	Characterization of high-photocurrent and high-speed INP-based uni-traveling-carrier photodiodes at 1.55 μm wavelength. Microwave and Optical Technology Letters, 2016, 58, 2156-2162.	1.4	2
36	Temperature-dependent phase noise properties of a two-section GaSb-based mode-locked laser emitting at 2 μm . Applied Physics Letters, 2020, 117, 141103.	3.3	2

#	ARTICLE	IF	CITATIONS
37	An enhanced charge carrier separation in a heterojunction solar cell with a metal oxide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 0, , 2100525.	1.8	2
38	Stable Mode-Locked Operation With High Temperature Characteristics of a Two-Section InGaAs/GaAs Double Quantum Wells Laser. <i>IEEE Access</i> , 2021, 9, 16608-16614.	4.2	1
39	Compact, Hybrid III-V/Silicon Vernier Laser Diode Operating From 1955â€“1992 nm. <i>IEEE Photonics Journal</i> , 2021, 13, 1-5.	2.0	1
40	Mode-locked operation characteristics of a monolithic integrated two-section InGaAs/GaAs double quantum wells laser with asymmetric waveguide. <i>Optics and Laser Technology</i> , 2022, 147, 107702.	4.6	1
41	Metal-insulator transition switching in VO_x heterojunctions. <i>Physical Review Materials</i> , 2022, 6, .	4.1	1
42	Modal gain characteristics of a two-section InGaAs/GaAs double quantum well passively mode-locked laser with asymmetric waveguide. <i>Scientific Reports</i> , 2022, 12, 5010.	3.3	1
43	Strain engineering for pseudo-magnetic fields in graphene. , 2022, , .		0